

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((silicon semiconductor) near1 substrate) same (variable near1 density near1 silicon) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:12
L2	0	((silicon semiconductor) near1 substrate) same (variable near1 silicon) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:09
L3	0	((silicon semiconductor) near1 substrate) same (variable near1 density) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:10
L4	0	((silicon semiconductor) near1 substrate) same (variable near1 porous) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:10
L5	1	((silicon semiconductor) near1 substrate) same (porous near1 silicon) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:11
L6	0	((silicon semiconductor) near1 substrate) same (variable near2 porous) same (integrated near circuit) same (temporary near1 (support layer)) same (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:11
L7	2575	438/406,455,458,761,960.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:12
L8	0	7 and (((silicon semiconductor) near1 substrate) same (variable near1 density near1 silicon) same (temporary near1 (support layer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:13

## EAST Search History

L9	0	7 and ((silicon semiconductor) near1 substrate) and (variable near2 porous) and (temporary near1 (support layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:13
L10	0	7 and ((silicon semiconductor) near1 substrate) and (porous near1 density) and (temporary near1 (support layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:15
L11	52	7 and ((silicon semiconductor) near1 substrate) and (porous near1 density)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:14
L12	12	7 and ((silicon semiconductor) near1 substrate) and (variable near2 porous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/20 12:15